Schottky Barrier Diode in a TO-220 Plastic Package.

ώ ̈ Ξ ̃Ạ / Absolute Maximum Ratings(Ta=25 ɹ)

Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	100	V
RMS Voltage	V_{RMS}	70	V
DC Blocking Voltage	V_{DC}	100	V
Average Rectified Forward Current	$I_{F(AV)}$	15	A
	$I_{F(AV)(total)}$	30	A
Non-Repetitive Peak Forward Surge Current	I_{FSM}	200	A
Peak Repetitive Forward Current	I_{FRM}	30	A
Repetitive Peak Reverse Surge Current	I_{RRM}	0.5	A
Thermal Resistance Junction to Case	$R_{\theta Jc}$	1.2	/W
Junction Temperature Range	T_j	-55 175	
Storage Temperature Range	T_{stg}	-55 175	

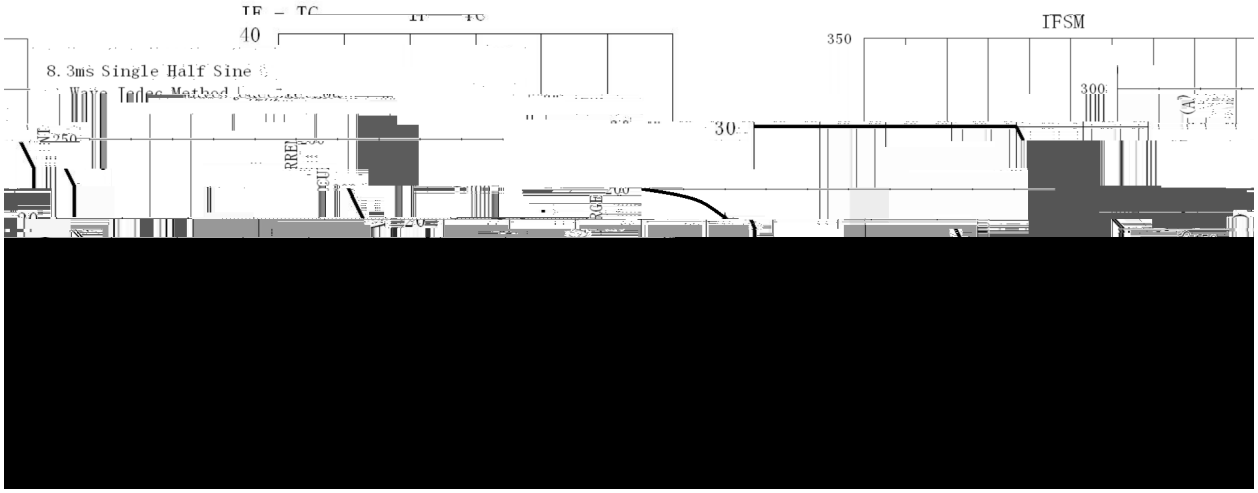
≠ ∧ Ξ ̃Ạ / Electrical Characteristics(Ta=25 ɹ)

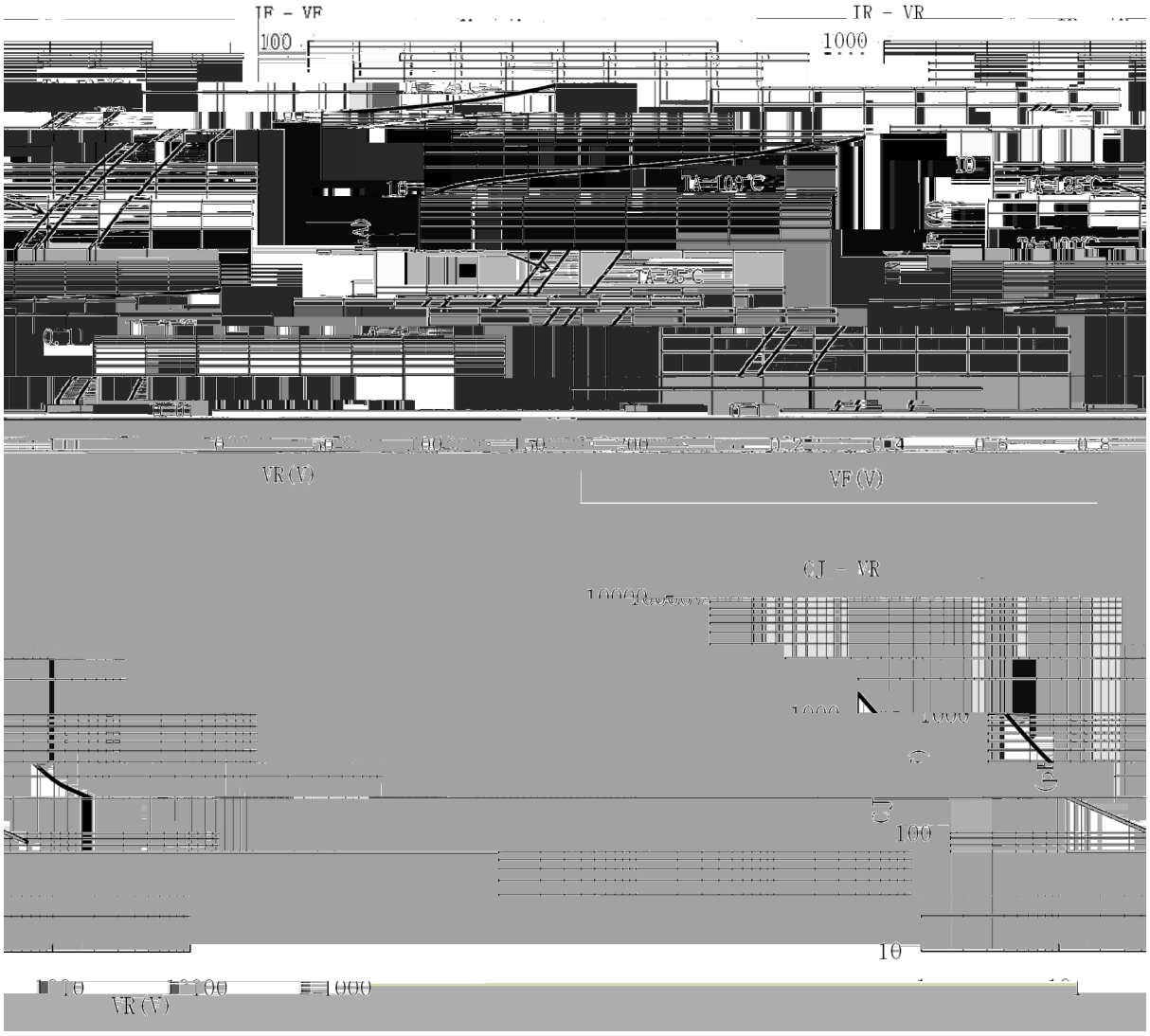
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward Voltage	V_F	I_F =15A(T_j=25)			0.91	V
		I_F =15A(T_j=125)			0.75	V
		I_F =30A(T_j=25)			1.05	V
		I_F =30A(T_j=125)			0.89	V
Instantaneous Reverse Current	I_R	T_C=25			0.05	mA
		T_C=125			20	mA

/Notes

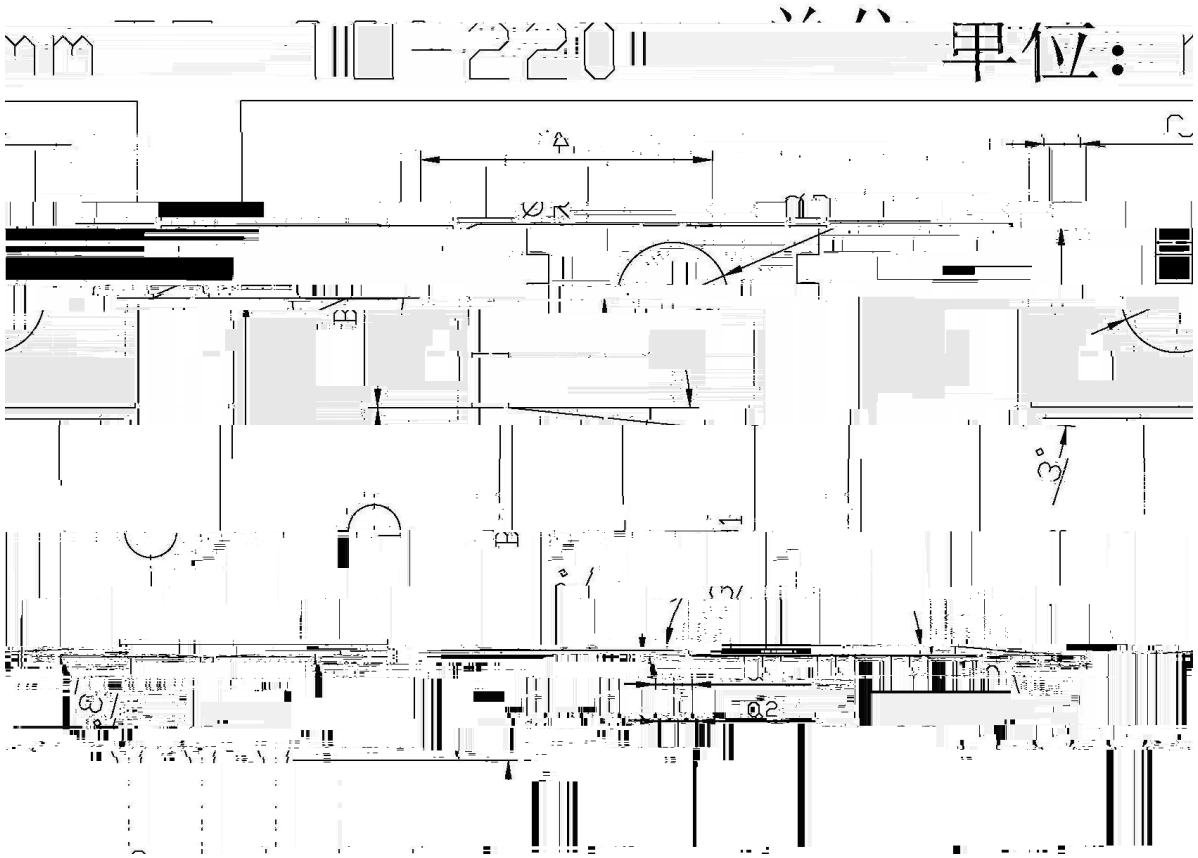
1. /Short duration pulse test used to minimize self-heating effect.
2. / Unless otherwise noted, values for the parameters of a single chip

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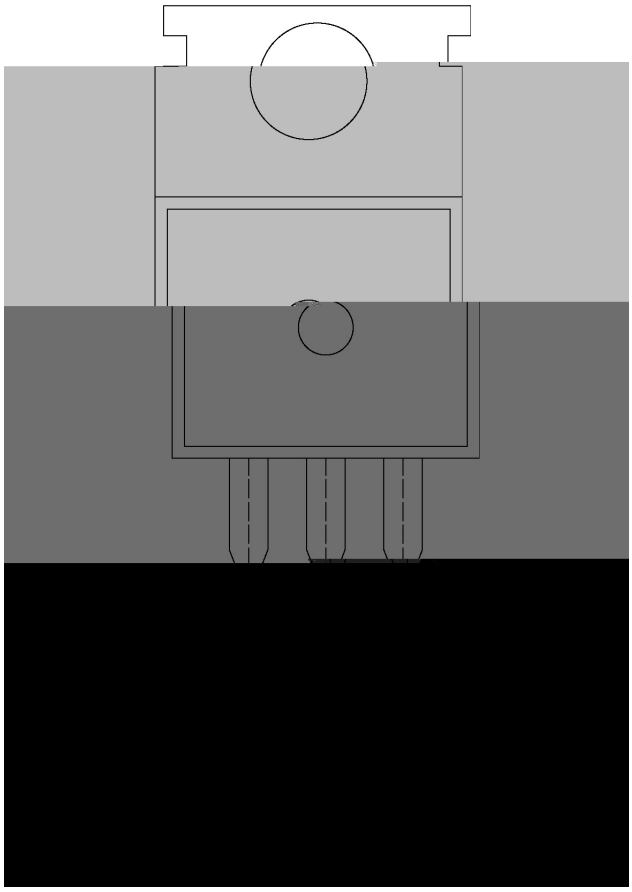




ᵘ ĖÒĻ ƒ / Package Dimensions



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